# **Darlington Transistors**

## **NPN Silicon**

## **Features**

• These are Pb-Free Devices\*

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CES</sub>	30	Vdc
Collector - Base Voltage	V <sub>CB</sub>	40	Vdc
Emitter -Base Voltage	V <sub>EB</sub>	10	Vdc
Collector Current - Continuous	Ic	1.0	Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above T <sub>A</sub> = 25°C	P <sub>D</sub>	625 12	mW mW/°C
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above T <sub>C</sub> = 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

## THERMAL CHARACTERISTICS

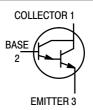
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

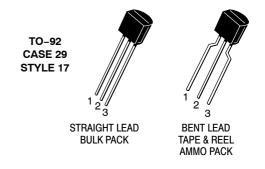
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



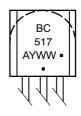
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## **MARKING DIAGRAM**



A = Assembly Location

Y = Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BC517G	TO-92 (Pb-Free)	5000 Units / Bulk
BC517RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC517ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I <sub>C</sub> = 2.0 mAdc, I <sub>BE</sub> = 0)	V <sub>(BR)</sub> CES	30	-	-	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \mu Adc, I_E = 0$ )	V <sub>(BR)</sub> CBO	40	-	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 100 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	10	-	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc)	I <sub>CES</sub>	_	-	500	nAdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	100	nAdc
Emitter Cutoff Current $(V_{CB} = 10 \text{ Vdc}, I_{C} = 0)$	I <sub>EBO</sub>	-	-	100	nAdc
ON CHARACTERISTICS (Note 1)	•	•			
DC Current Gain (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 2.0 Vdc)	h <sub>FE</sub>	30,000	-	-	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0.1 mAdc)	V <sub>CE(sat)</sub>	-	-	1.0	Vdc
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE(on)</sub>	-	-	1.4	Vdc
SMALL-SIGNAL CHARACTERISTICS	·	-			
Current-Gain - Bandwidth Product (Note 2) (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	-	200	-	MHz

<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle 2.0%. 2.  $f_T = |h_{fe}| \bullet f_{test}$ 

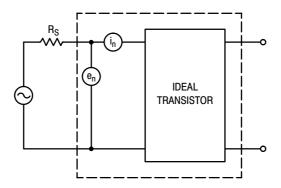


Figure 1. Transistor Noise Model

## **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

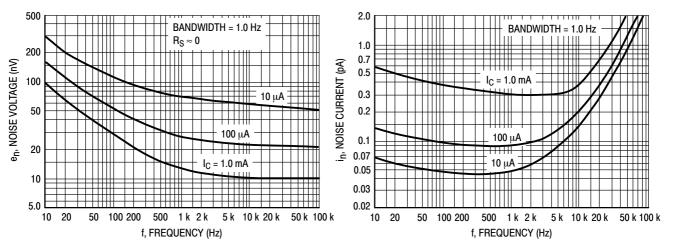


Figure 2. Noise Voltage

Figure 3. Noise Current

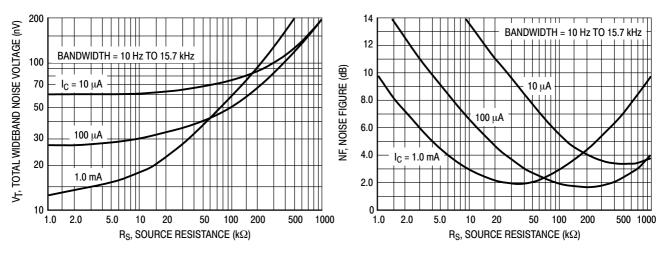
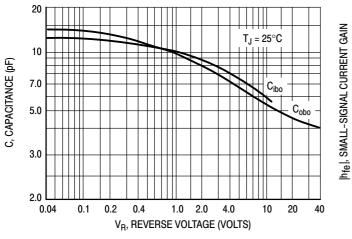


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

## **SMALL-SIGNAL CHARACTERISTICS**



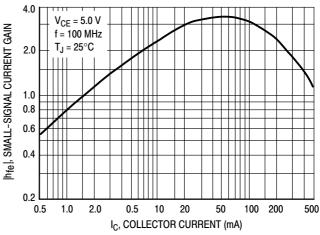
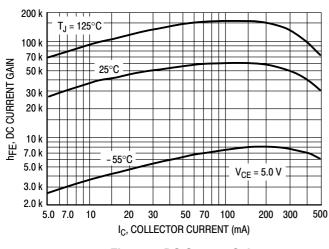


Figure 6. Capacitance

Figure 7. High Frequency Current Gain



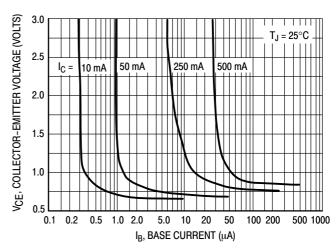
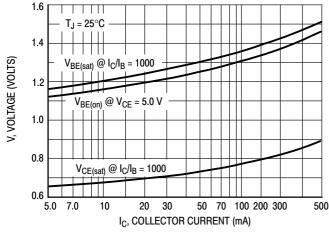


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region



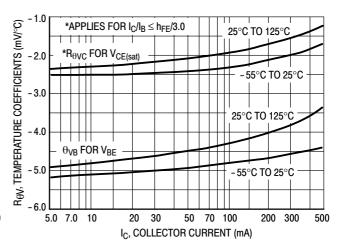


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

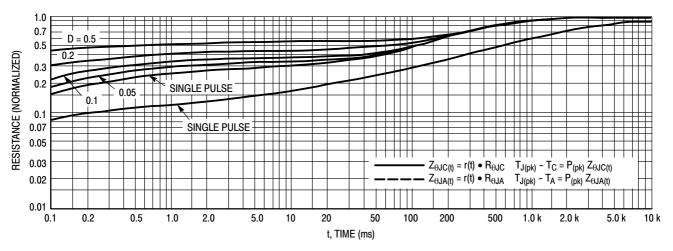


Figure 12. Thermal Response

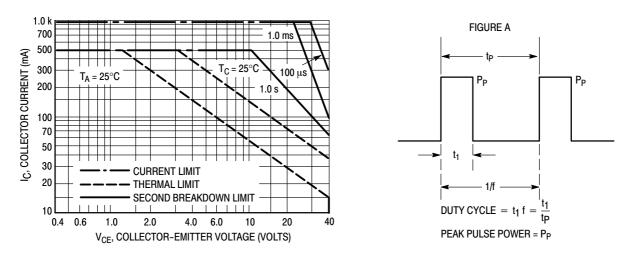
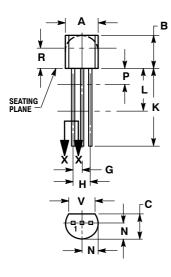


Figure 13. Active Region Safe Operating Area Design Note: Use of Transient Thermal Resistance Data

### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM** 



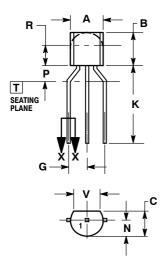
STRAIGHT LEAD **BULK PACK** 



### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	



**BENT LEAD** TAPE & REEL AMMO PACK



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

-			
	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

STYLE 17:

COLLECTOR PIN 1.

BASE

EMITTER

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BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143TF3T5G NSBA143ZF3T5G NSBC114EF3T5G NSBC114YF3T5G
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SMUN5335DW1T1G NSBA114YF3T5G NSBC114TF3T5G